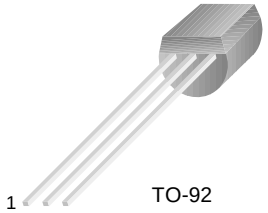
FAIRCHILD
SEMICONDUCTOR®

FJN3310R

Switching Application (Bias Resistor Built In)

- Switching circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor (R=10KΩ)
- Complement to FJN4310R



TO-92

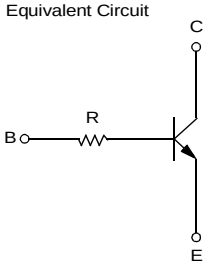
1. Emitter 2. Collector 3. Base

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	100	mA
P_C	Collector Power Dissipation	300	mW
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	-55 ~ 150	°C

Equivalent Circuit



Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	I_C=100μA, I_E=0	40			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_E=1mA, I_B=0	40			V
I_{CBO}	Collector Cut-off Current	V_{CB}=30V, I_E=0			0.1	μA
h_{FE}	DC Current Gain	V_{CE}=5V, I_C=1mA	100		600	
V_{CE} (sat)	Collector-Emitter Saturation Voltage	I_C=10mA, I_B=1mA			0.3	V
C_{ob}	Output Capacitance	V_{CB}=10V, I_E=0 f=1MHz		3.7		pF
f_T	Current Gain Bandwidth Product	V_{CE}=10V, I_C=5mA		250		MHz
R	Input Resistor		7	10	13	KΩ

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Typical Characteristics

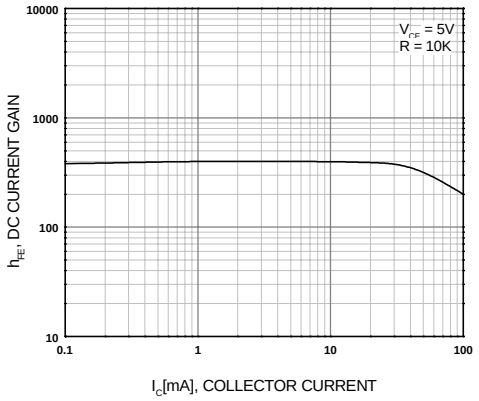


Figure 1. DC current Gain

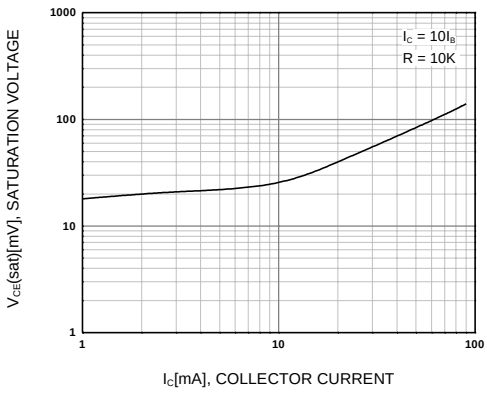


Figure 2. Collector-Emitter Saturation Voltage

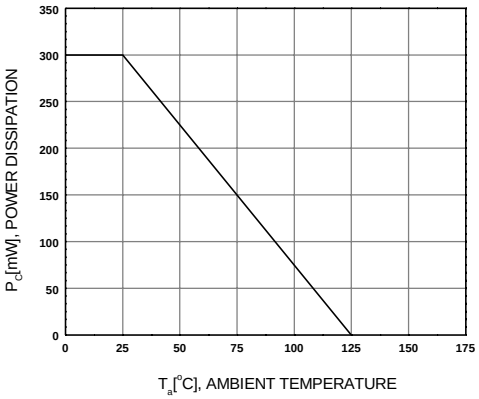
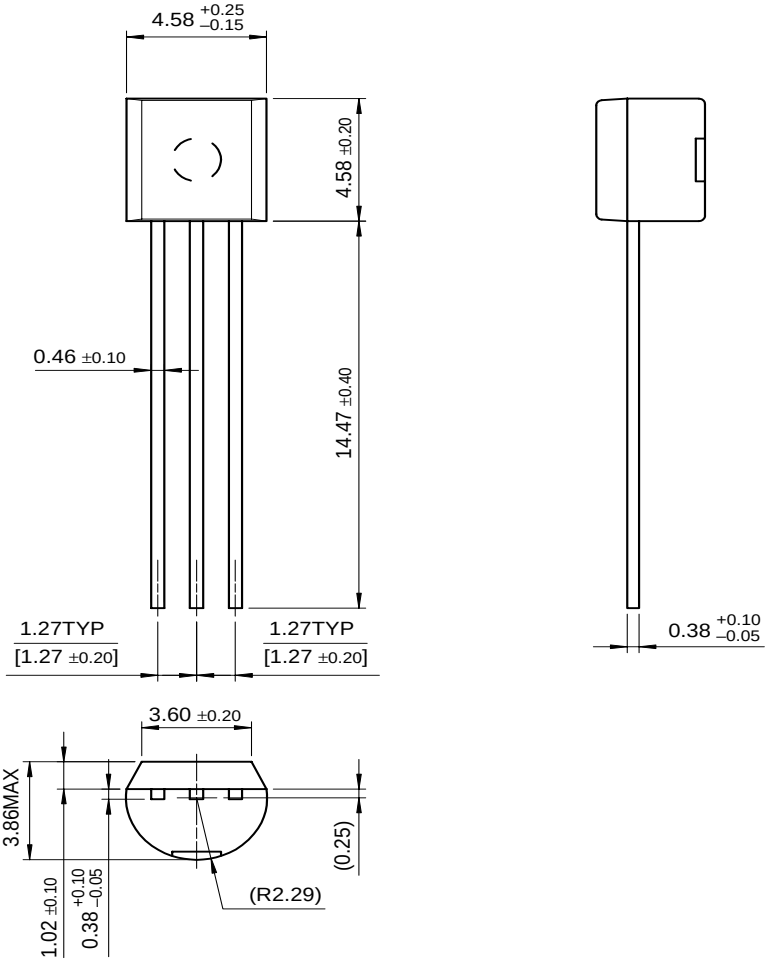


Figure 3. Power Derating

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Package Dimensions

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Dimensions in Millimeters

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CROSSVOLT™	FRFET™	MicroPak™	QFET™	SuperSOT™-8
DOME™	GlobalOptoisolator™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
E^2CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	I^2C™	OCX™	RapidConfigure™	UHC™
Across the board. Around the world.™		OCXPro™	RapidConnect™	UltraFET®
The Power Franchise™		OPTOLOGIC®	SILENT SWITCHER®	VCX™
Programmable Active Droop™		OPTOPLANAR™	SMART START™	

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Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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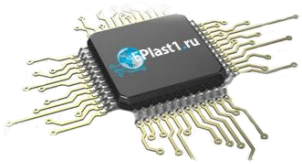
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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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